



NAVITAS MAKES LENOVO AND XIAOMI CHARGERS FASTER, SMALLER AND MORE POWERFUL

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New Gallium Nitride (GaNFast) technology dominates silicon in consumer mobile fast charger market

EL SEGUNDO, Calif.-(PRWeb)—[Navitas Semiconductor](#) today announced that it will [showcase](#) world-leading GaNFast™ power IC technology in addition to partnerships with major electronics brands at the SEMICON China 2020 exhibition and conference in Shanghai. Gallium Nitride (GaN) is a next-generation semiconductor technology that runs up to 20x faster than old, slow silicon (Si), and enables 3x more power, which translates to up to 3x faster charging in half the size & weight.

Forty years ago, the power electronics industry experienced an extraordinary and disruptive change with the introduction silicon MOSFET technology. In the following decade, the power supply industry experienced a 5x increase in power density, a 5x reduction in losses in energy savings and a 3x reduction in costs. However, the next 30 years saw heavy investment that yielded smaller and smaller improvements. Now, GaN Power ICs with monolithic integration of GaN FET, GaN digital and GaN analog circuits have driven a new generation of high-frequency, high-efficiency and very high-density power converters.

“All new flagship fast chargers from top mobile OEMs use GaN technology,” noted Charles ZHA, VP & General Manager of Navitas China. “For the Thinkplus 65W GaN ‘Lipstick’ fast charger, GaNFast power ICs enabled Lenovo to deliver the world’s smallest, lightest charger to power the new Carbon X1 and Yoga laptops.”

GaNFast power ICs enable next-generational upgrades across diverse markets from 25-100W consumer and mobile [USB-C fast chargers](#) and adapters for smartphones and laptops, to 200-800W TV and all-in-one computers and on up to multi-kW EV, industrial and datacenter power supplies.

Paper details:

- Title: “GaN Power ICs Drive Fast Charger Innovation and Market Adoption”
- Presenter: Charles Zha 查莹杰, VP, General Manager of China, Navitas Semiconductor
- Date/time: June 29th, 2020, at 13:30.
- Forum/Session: Power & Compound Semiconductor International Forum 2020 / Wide Band Gap Semiconductors & Emerging Power Devices.
- Location: Shanghai Pudong Kerry Hotel, Ballroom 4, No.1388 Huamu Road Pudong, Shanghai, PRC.

To meet with Navitas at SEMICON China, please contact +1 ThinkGaNIC (844-654-2642) or email Info@NavitasSemi.com.

About Navitas:

[Navitas Semiconductor Inc.](#) is the world’s first and only GaN Power IC company, founded in 2014 and based in El Segundo, CA, USA. Navitas has a strong and growing team of power semiconductor industry experts with a combined 200 years of experience in materials, devices, applications, systems and marketing, plus a proven record of innovation with over 300 patents among its founders. GaN power ICs monolithically-integrate power, analog and logic circuits to enable faster charging, higher power density and greater energy savings for mobile, consumer, enterprise, eMobility and new energy markets. Over 100 Navitas patents are issued or pending.

About SEMICON China:

[SEMICON China](#) runs from June 27th – 29th at the Shanghai New International Expo Center. It is the world’s largest semiconductor industry platform, where market, technology and investment opportunities come together. High level executives from the industry, science and government will present their view and showcase their latest products and technology on this premier stage.

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